

FORM PTO 1449 (modified)

ATTY DOCKET NO.

03500.010530.4

APPLICATION NO.

09/161,774

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

APPLICANT

KIYOFUMI SAKAGUCHI, ET AL.

FILING DATE

September 29, 1998

GROUP

2823

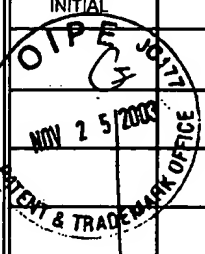
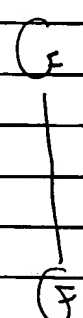
LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

Submitted: November 25, 2003

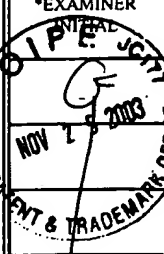
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